PRELIMINARY **CY62256V**

32K x 8 Static RAM

Features

- **55, 70 ns access time**
- **CMOS for optimum speed/power**
- **Wide voltage range: 2.7V–3.6V**
- **Low active power (70 ns, LL version) — 108 mW (max.)**
- **Low standby power (70 ns, LL version) — 18 µW (max.)**
- **Easy memory expansion with $\overline{CE}$ and $\overline{OE}$ features**
- **TTL-compatible inputs and outputs**
- **Automatic power-down when deselected**

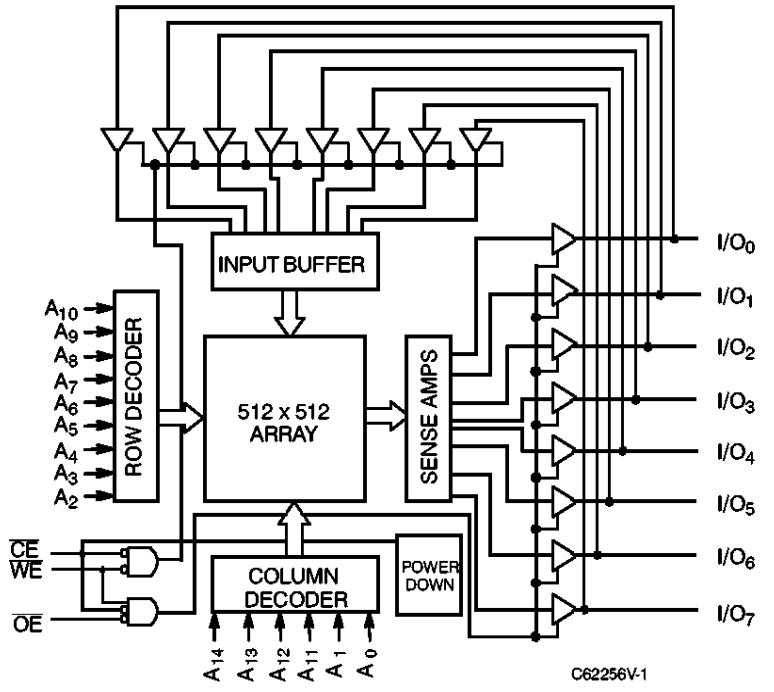
Functional Description

The CY62256V is a high-performance CMOS static RAM organized as 32,768 words by 8 bits. Easy memory expansion is provided by an active LOW chip enable ($\overline{CE}$) and active LOW output enable ($\overline{OE}$) and three-state drivers. This device has an automatic power-down feature, reducing the power consumption by 98% when deselected. The CY62256V is in the standard 450-mil-wide (300-mil body width) SOIC, TSOP, and reverse TSOP packages.

An active LOW write enable signal ($\overline{WE}$) controls the writing/reading operation of the memory. When $\overline{CE}$ and $\overline{WE}$ inputs are both LOW, data on the eight data input/output pins (I/O_0 through I/O_7) is written into the memory location addressed by the address present on the address pins (A_0 through A_{14}). Reading the device is accomplished by selecting the device and enabling the outputs, $\overline{CE}$ and $\overline{OE}$ active LOW, while $\overline{WE}$ remains inactive or HIGH. Under these conditions, the contents of the location addressed by the information on address pins is present on the eight data input/output pins.

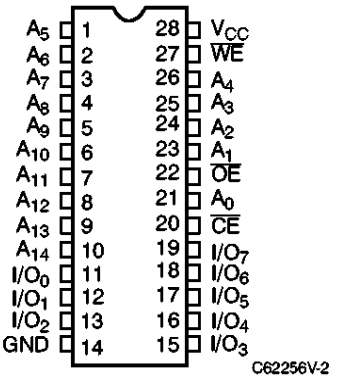
The input/output pins remain in a high-impedance state unless the chip is selected, outputs are enabled, and write enable ($\overline{WE}$) is HIGH. A die coat is used to ensure alpha immunity.

Logic Block Diagram



Pin Configurations

SOIC
Top View



Pin Configurations (continued)

TSOP
Top View

C62256V-3

TSOP Reversed
Top View

C62256V-4

Selection Guide

		CY62256V−55	CY62256V−70
Maximum Access Time (ns)		55	70
Maximum Operating Current (mA)		50	50
	L	50	50
	LL	30	30
Maximum Standby Current (μA)		500	500
	L	50	50
	LL	5	5

Shaded area contains advanced information.

Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature ..... −65°C to +150°C

Ambient Temperature with Power Applied ..... 0°C to +70°C

Supply Voltage to Ground Potential (Pin 28 to Pin 14) ..... −0.5V to +4.6V

DC Voltage Applied to Outputs in High Z State[1] ..... −0.5V to V_{CC} + 0.5V

DC Input Voltage[1] ..... −0.5V to V_{CC} + 0.5V

Output Current into Outputs (LOW) ..... 20 mA

Static Discharge Voltage ..... >2001V (per MIL-STD-883, Method 3015)

Latch-Up Current ..... >200 mA

Operating Range

Range	Ambient Temperature	V_{CC}
Commercial	0°C to +70°C	2.7V to 3.6V

Notes:
1. V_{IL} (min.) = −2.0V for pulse durations of less than 20 ns.

Electrical Characteristics Over the Operating Range

Parameter	Description	Test Conditions		CY62256V−55 Min.	CY62256V−55 Max.	CY62256V−70 Min.	CY62256V−70 Max.	Unit
V_{OH}	Output HIGH Voltage	V_{CC} = Min., I_{OH} = −1.0 mA		2.4		2.4		V
V_{OL}	Output LOW Voltage	V_{CC} = Min., I_{OL} = 2.1 mA			0.4		0.4	V
V_{IH}	Input HIGH Voltage			2.2	V_{CC} +0.3V	2.2	V_{CC} +0.3V	V
V_{IL}	Input LOW Voltage			−0.5	0.8	−0.5	0.8	V
I_{IX}	Input Load Current	GND ≤ V_I ≤ V_{CC}		−1	+1	−1	+1	μA
I_{OZ}	Output Leakage Current	GND ≤ V_O ≤ V_{CC}, Output Disabled		−5	+5	−5	+5	μA
I_{OS}	Output Short Circuit Current[2]	V_{CC} = Max., V_{OUT} = GND			−200		−200	mA
I_{CC}	V_{CC} Operating Supply Current	V_{CC} = Max., I_{OUT} = 0 mA, f = f_{MAX} = $1/t_{RC}$			50		50	mA
			L		50		50	
			LL		30		30	
I_{SB1}	Automatic CE Power-Down Current—TTL Inputs	Max. V_{CC}, $\overline{CE}$ ≥ V_{IH}, V_{IN} ≥ V_{IH} or V_{IN} ≤ V_{IL}, f = f_{MAX}			5		5	mA
			L		3		3	
			LL		1		1	
I_{SB2}	Automatic CE Power-Down Current—CMOS Inputs	Max. V_{CC}, $\overline{CE}$ ≥ V_{CC} − 0.3V V_{IN} ≥ V_{CC} − 0.3V or V_{IN} ≤ 0.3V, f = 0			500		500	μA
			L		50		50	
			LL		5		5	

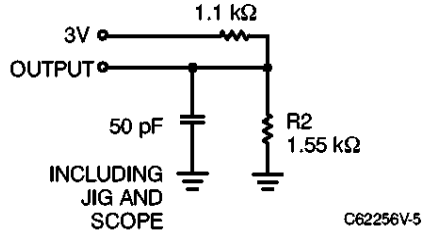
Shaded area contains advanced information.

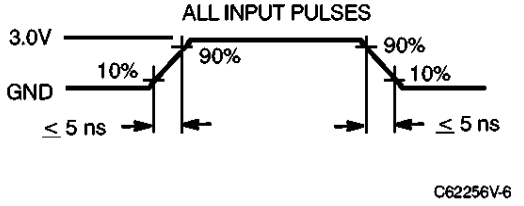
Capacitance[3]

Parameter	Description	Test Conditions	Max.	Unit
C_{IN}	Input Capacitance	T_A = 25°C, f = 1 MHz, V_{CC} = 3.0V	6	pF
C_{OUT}	Output Capacitance		8	pF

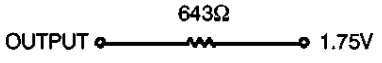
Note:
2. Not more than one output should be shorted at one time. Duration of the short circuit should not exceed 30 seconds.
3. Tested initially and after any design or process changes that may affect these parameters.

AC Test Loads and Waveforms





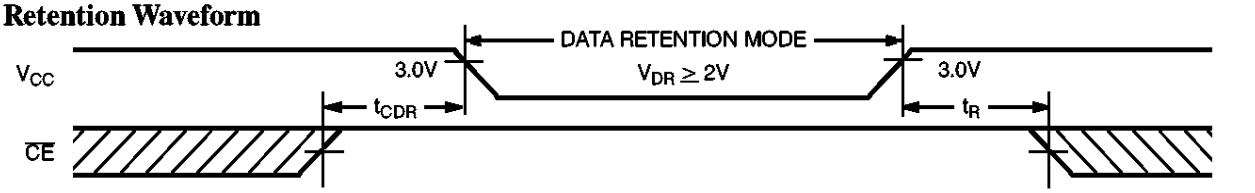
Equivalent to: THÉVENIN EQUIVALENT



Data Retention Characteristics (Over the Operating Range)

Parameter	Description		Conditions[4]	Min.	Max.	Unit
V_{DR}	V_{CC} for Data Retention			2.0		V
I_{CCDR}	Data Retention Current		$V_{CC} = V_{DR} = 3.0V$, $\overline{CE} \geq V_{CC} - 0.3V$, $V_{IN} \geq V_{CC} - 0.3V$ or $V_{IN} \leq 0.3V$		200	µA
		L			20	µA
		LL			5	µA
t_{CDR}[3]	Chip Deselect to Data Retention Time			0		ns
t_R[3]	Operation Recovery Time			t_{RC}		ns

Data Retention Waveform



C62256V-7

Switching Characteristics Over the Operating Range[5]

Parameter	Description	CY62256V−55		CY62256V−70		Unit
		Min.	Max.	Min.	Max.	
READ CYCLE						
t_{RC}	Read Cycle Time	55		70		ns
t_{AA}	Address to Data Valid		55		70	ns
t_{OHA}	Data Hold from Address Change	3		3		ns
t_{ACE}	$\overline{CE}$ LOW to Data Valid		55		70	ns
t_{DOE}	$\overline{OE}$ LOW to Data Valid		25		35	ns
t_{LZOE}	$\overline{OE}$ LOW to Low Z[6]	3		3		ns
t_{HZOE}	$\overline{OE}$ HIGH to High Z[6, 7]		20		25	ns
t_{LZCE}	$\overline{CE}$ LOW to Low Z[6]	3		3		ns
t_{HZCE}	$\overline{CE}$ HIGH to High Z[6, 7]		20		25	ns
t_{PU}	$\overline{CE}$ LOW to Power-Up	0		0		ns
t_{PD}	$\overline{CE}$ HIGH to Power-Down		55		70	ns

Shaded area contains advanced information.

Notes:

4. No input may exceed V_{CC}+0.3V.
5. Test conditions assume signal transition time of 5 ns or less timing reference levels of 1.5V, input pulse levels of 0 to 3.0V, and output loading of the specified I_{OL}/I_{OH} and 100-pF load capacitance.
6. At any given temperature and voltage condition, t_{HZCE} is less than t_{LZCE}, t_{HZOE} is less than t_{LZOE}, and t_{HZWE} is less than t_{LZWE} for any given device.
7. t_{HZOE}, t_{HZCE}, and t_{HZWE} are specified with C_L = 5 pF as in part (b) of AC Test Loads. Transition is measured ±500 mV from steady-state voltage.

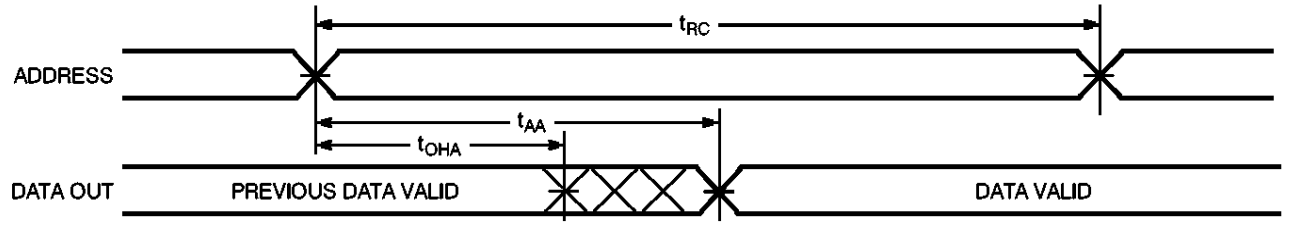
Switching Characteristics Over the Operating Range[5]

Parameter	Description	CY62256V−55		CY62256V−70		Unit
		Min.	Max.	Min.	Max.	
WRITE CYCLE[8, 9]						
t_{WC}	Write Cycle Time	55		70		ns
t_{SCE}	$\overline{CE}$ LOW to Write End	45		60		ns
t_{AW}	Address Set-Up to Write End	45		60		ns
t_{HA}	Address Hold from Write End	0		0		ns
t_{SA}	Address Set-Up to Write Start	0		0		ns
t_{PWE}	$\overline{WE}$ Pulse Width	40		50		ns
t_{SD}	Data Set-Up to Write End	25		30		ns
t_{HD}	Data Hold from Write End	0		0		ns
t_{HZWE}	$\overline{WE}$ LOW to High Z[6, 7]		20		25	ns
t_{LZWE}	$\overline{WE}$ HIGH to Low Z[6]	3		3		ns

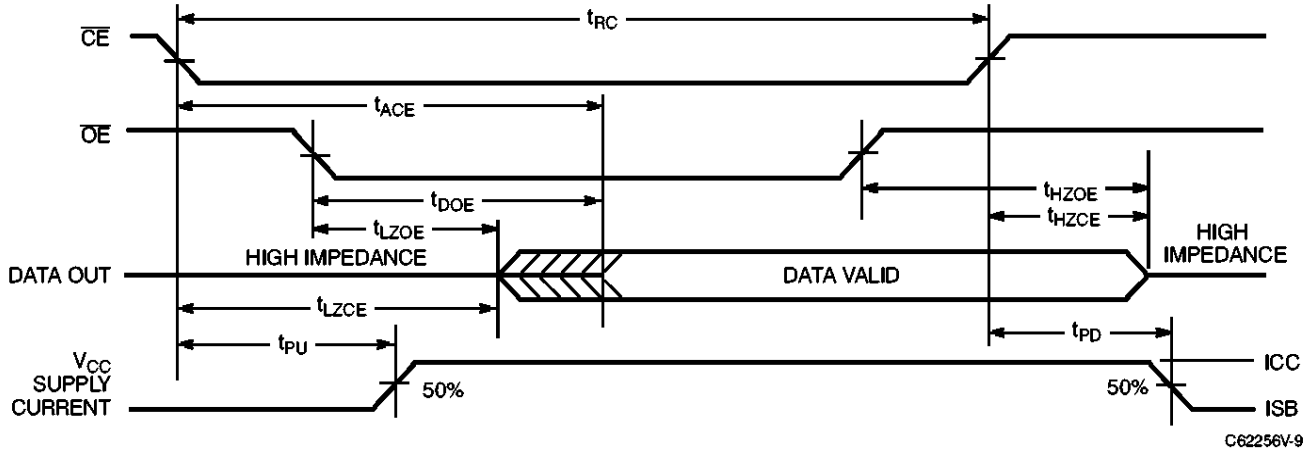
Shaded area contains advanced information.

Switching Waveforms

Read Cycle No. 1[10, 11]



Read Cycle No. 2[11, 12]

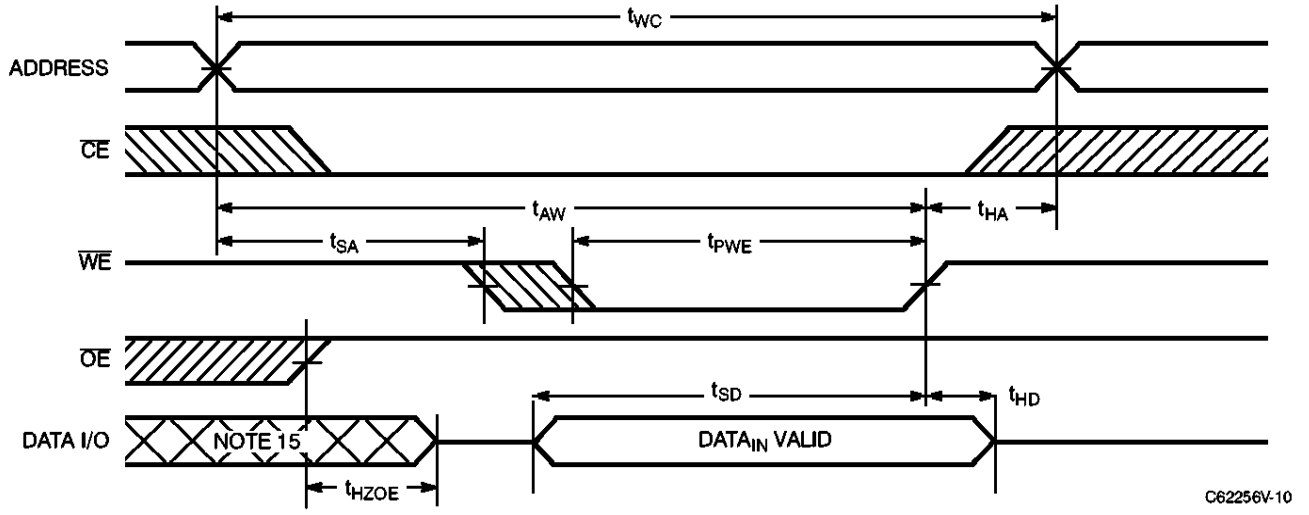


Notes:

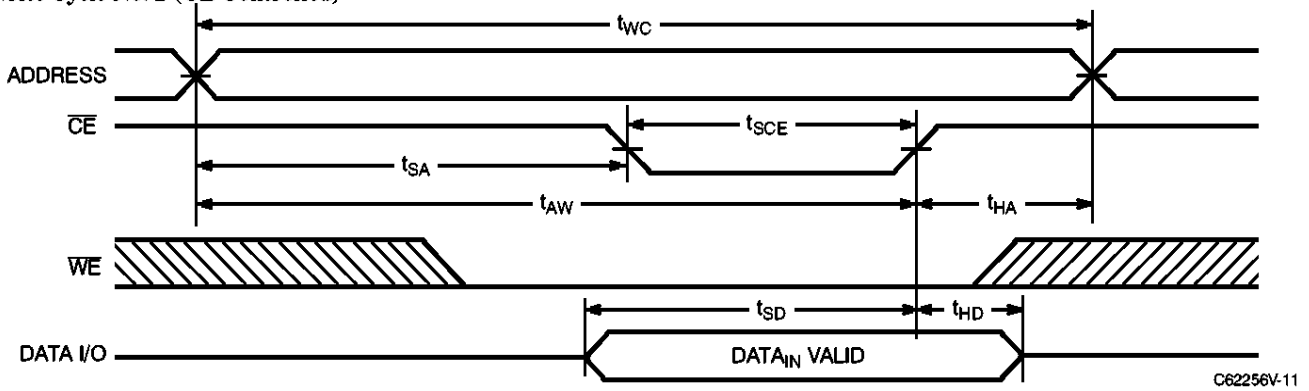
8. The internal write time of the memory is defined by the overlap of $\overline{CE}$ LOW and $\overline{WE}$ LOW. Both signals must be LOW to initiate a write and either signal can terminate a write by going HIGH. The data input set-up and hold timing should be referenced to the rising edge of the signal that terminates the write.
9. The minimum write cycle time for write cycle #3 ($\overline{WE}$ controlled, $\overline{OE}$ LOW) is the sum of t_{HZWE} and t_{SD}.
10. Device is continuously selected. $\overline{OE}$, $\overline{CE}$ = V_{IL}.
11. $\overline{WE}$ is HIGH for read cycle.
12. Address valid prior to or coincident with $\overline{CE}$ transition LOW.

Switching Waveforms (continued)

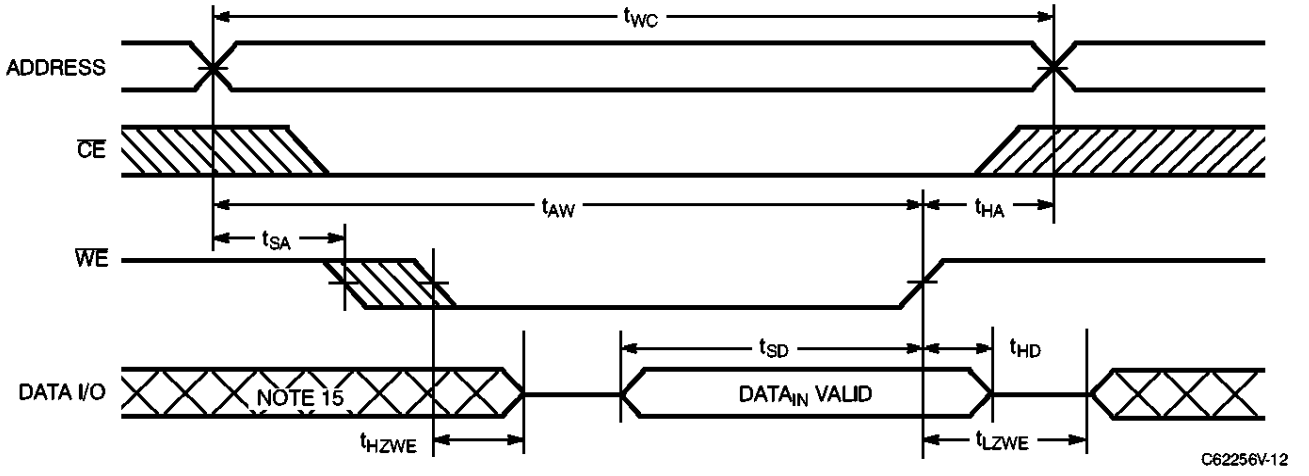
Write Cycle No. 1 ($\overline{WE}$ Controlled)[8, 13, 14]



Write Cycle No. 2 ($\overline{CE}$ Controlled)[8, 13, 14]



Write Cycle No. 3 ($\overline{WE}$ Controlled, $\overline{OE}$ LOW)[9, 14]

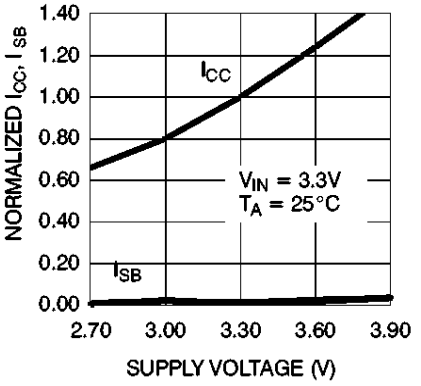


Notes:

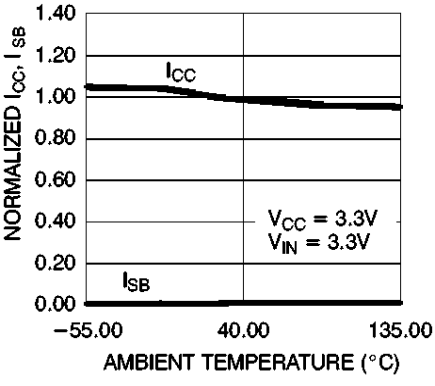
13. Data I/O is high impedance if $\overline{OE}$ = V_{IH}.
14. If $\overline{CE}$ goes HIGH simultaneously with $\overline{WE}$ HIGH, the output remains in a high-impedance state.
15. During this period, the I/Os are in output state and input signals should not be applied.

Typical DC and AC Characteristics

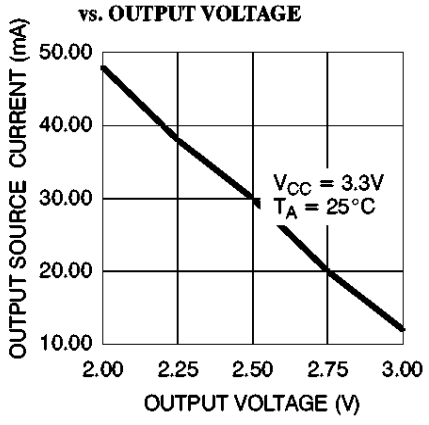
NORMALIZED SUPPLY CURRENT vs. SUPPLY VOLTAGE



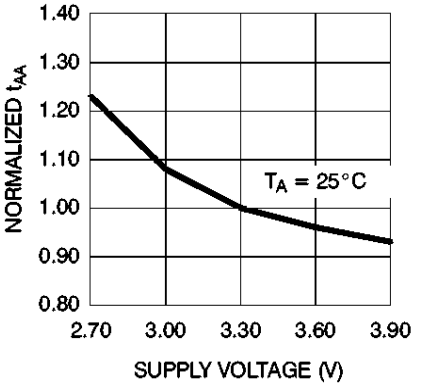
NORMALIZED SUPPLY CURRENT vs. AMBIENT TEMPERATURE



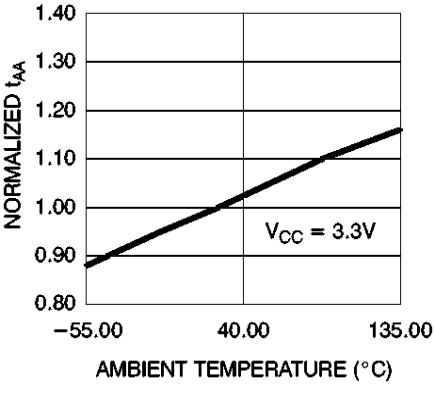
OUTPUT SOURCE CURRENT vs. OUTPUT VOLTAGE



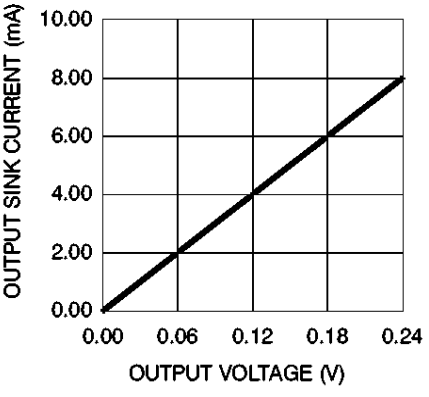
NORMALIZED ACCESS TIME vs. SUPPLY VOLTAGE



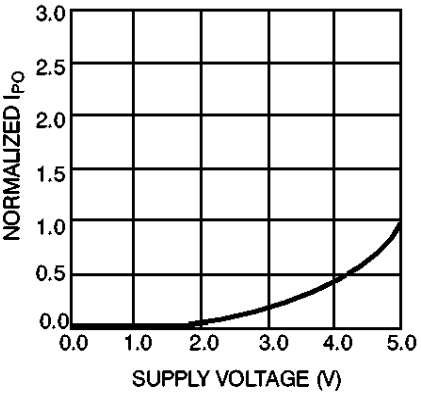
NORMALIZED ACCESS TIME vs. AMBIENT TEMPERATURE



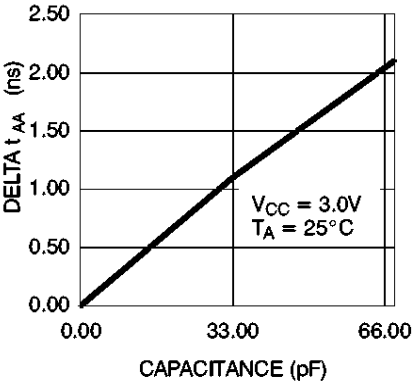
OUTPUT SINK CURRENT vs. OUTPUT VOLTAGE



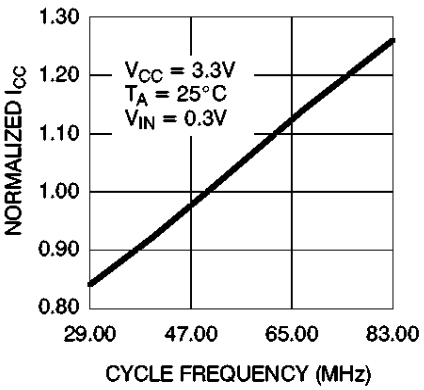
TYPICAL POWER-ON CURRENT vs. SUPPLY VOLTAGE



TYPICAL ACCESS TIME CHANGE vs. OUTPUT LOADING



NORMALIZED I_{CC} vs. CYCLE TIME



Truth Table

$\overline{CE}$	$\overline{WE}$	$\overline{OE}$	Inputs/Outputs	Mode	Power
H	X	X	High Z	Deselect/Power-Down	Standby (I_{SB})
L	H	L	Data Out	Read	Active (I_{CC})
L	L	X	Data In	Write	Active (I_{CC})
L	H	H	High Z	Deselect, Output Disabled	Active (I_{CC})

Ordering Information

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
55	CY62256V−55SNC	S22	28-Lead 450-Mil (300-Mil Body Width) SOIC	Commercial
	CY62256VL−55SNC	S22	28-Lead 450-Mil (300-Mil Body Width) SOIC	
	CY62256VLL−55SNC	S22	28-Lead 450-Mil (300-Mil Body Width) SOIC	
	CY62256V−55RZC	RZ28	28-Lead Reverse Thin Small Outline Package	
	CY62256VL−55RZC	RZ28	28-Lead Reverse Thin Small Outline Package	
	CY62256VLL−55RZC	RZ28	28-Lead Reverse Thin Small Outline Package	
	CY62256V−55ZC	Z28	28-Lead Thin Small Outline Package	
	CY62256VL−55ZC	Z28	28-Lead Thin Small Outline Package	
	CY62256VLL−55ZC	Z28	28-Lead Thin Small Outline Package	
70	CY62256V−70SNC	S22	28-Lead 450-Mil (300-Mil Body Width) SOIC	Commercial
	CY62256VL−70SNC	S22	28-Lead 450-Mil (300-Mil Body Width) SOIC	
	CY62256VLL−70SNC	S22	28-Lead 450-Mil (300-Mil Body Width) SOIC	
	CY62256V−70RZC	RZ28	28-Lead Reverse Thin Small Outline Package	
	CY62256VL−70RZC	RZ28	28-Lead Reverse Thin Small Outline Package	
	CY62256VLL−70RZC	RZ28	28-Lead Reverse Thin Small Outline Package	
	CY62256V−70ZC	Z28	28-Lead Thin Small Outline Package	
	CY62256VL−70ZC	Z28	28-Lead Thin Small Outline Package	
	CY62256VLL−70ZC	Z28	28-Lead Thin Small Outline Package	

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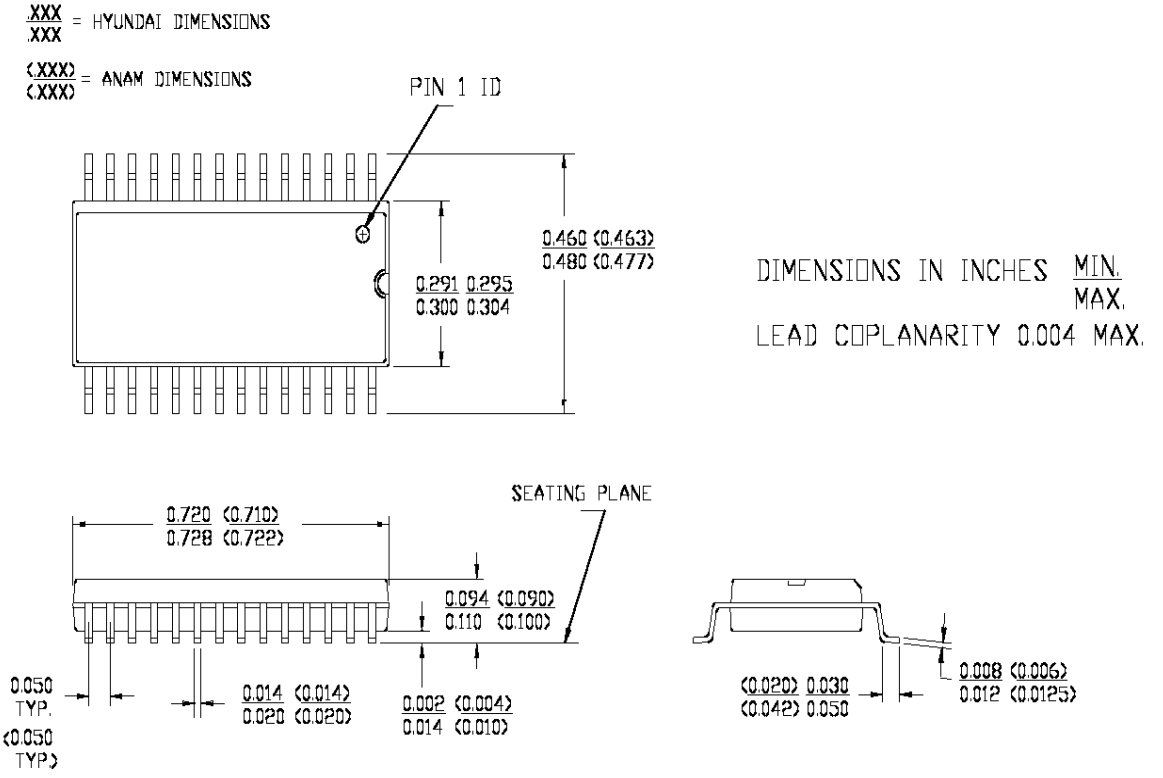
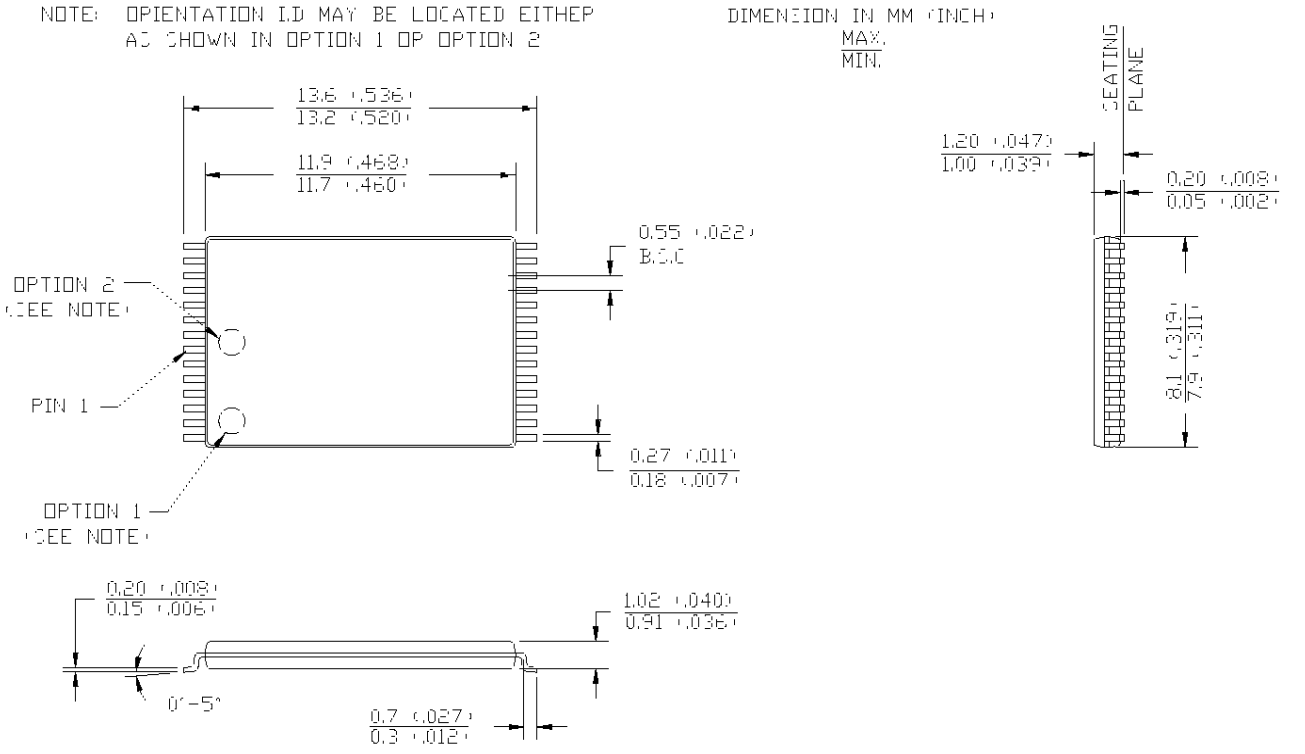
Package Diagrams

28-Lead 450-Mil (300-Mil Body Width) SOIC S22



28-Lead Reverse Thin Small Outline Package RZ28



Package Diagrams (continued)

28-Lead Thin Small Outline Package Z28